

BAS32L

High-speed switching diode

Rev. 04 — 22 March 2005

Product data sheet

1. Product profile

1.1 General description

Single high-speed switching diode, fabricated in planar technology, and encapsulated in a small hermetically sealed glass SOD80C SMD package.

1.2 Features

- Small hermetically sealed glass SMD package
- High switching speed: ≤ 4 ns
- Continuous reverse voltage: ≤ 75 V
- Repetitive peak reverse voltage: ≤ 100 V
- Repetitive peak forward current: ≤ 450 mA

1.3 Applications

- High-speed switching
- Inverse-polarity protection

1.4 Quick reference data

Table 1: Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current		[1] -		200	mΑ
I _{FRM}	repetitive peak forward current	JA =-	-	-	450	mA
V_R	reverse voltage		-	-	75	V
V _F	forward voltage	$I_F = 100 \text{ mA}$	-	-	1000	mV
t _{rr}	reverse recovery time		[2] _	-	4	ns

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] When switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100$ Ω ; measured at $I_R = 1$ mA





Philips Semiconductors

BAS32L

2. Pinning information

Table 2: Pinning

	9		
Pin	Description	Simplified outline	Symbol
1	cathode	[1]	1.4
2	anode	k a	+
			sym006

^[1] The marking band indicates the cathode.

3. Ordering information

Table 3: Ordering information

Type number	Package		
	Name	Description	Version
BAS32L	-	hermetically sealed glass surface mounted package; 2 connectors	SOD80C

4. Marking

Table 4: Marking codes

Type number	Marking code [1]
BAS32L	Marking band

^[1] black: made in Philippines brown: made in China

5. Limiting values

Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	100	V
V_R	reverse voltage		-	75	V
I _F	forward current		<u>[1]</u> _	200	mA
I _{FRM}	repetitive peak forward current		-	450	mA
I _{FSM}	non-repetitive peak forward current	square wave	[2]		
		$t_p = 1 \mu s$	-	4	Α
		$t_p = 1 \text{ ms}$	-	1	Α
		t _p = 1 s	-	0.5	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	<u>[1]</u> _	500	mW

High-speed switching diode

Philips Semiconductors

BAS32L

High-speed switching diode

Table 5: Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	200	°C
T _{amb}	ambient temperature		-65	+200	°C
T _{stg}	storage temperature		-65	+200	°C

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 6: Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	350	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	300	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 7: Characteristics

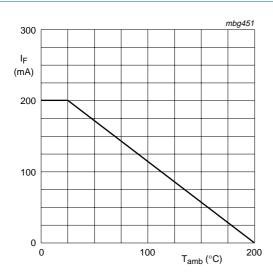
T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F	forward voltage	I _F = 5 mA	620	-	750	mV
		$I_F = 100 \text{ mA}$	-	-	1000	mV
		$I_F = 100 \text{ mA}; T_j = 100 ^{\circ}\text{C}$	-	-	930	mV
I _R	reverse current	V _R = 20 V	-	-	25	nA
		V _R = 75 V	-	-	5	μΑ
		$V_R = 20 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	50	μΑ
		$V_R = 75 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	100	μΑ
C _d	diode capacitance	$V_R = 0 \ V; f = 1 \ MHz$	-	-	2	pF
t _{rr}	reverse recovery time		[1] -	-	4	ns
V_{FR}	forward recovery voltage		[2] _	-	2.5	V

^[1] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA

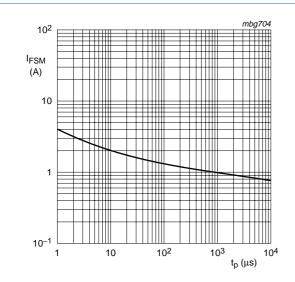
^[2] $T_i = 25$ °C prior to surge

^[2] When switched from I_F = 50 mA; t_r = 20 ns



Mounted on an FR4 PCB; standard footprint

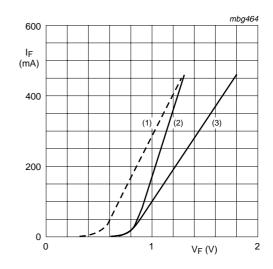
Fig 1. Maximum permissible forward current as a function of ambient temperature



Based on square wave currents

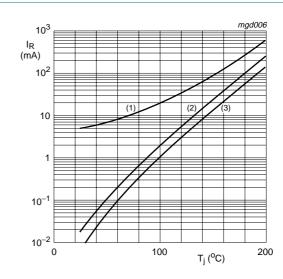
 $T_j = 25$ °C prior to surge

Fig 3. Maximum permissible non-repetitive peak forward current as a function of pulse duration



- (1) $T_i = 175$ °C; typical values
- (2) $T_i = 25$ °C; typical values
- (3) $T_i = 25 \,^{\circ}C$; maximum values

Fig 2. Forward current as a function of forward voltage



- (1) $V_R = 75 \text{ V}$; maximum values
- (2) $V_R = 75 V$; typical values
- (3) V_R = 20 V; typical values

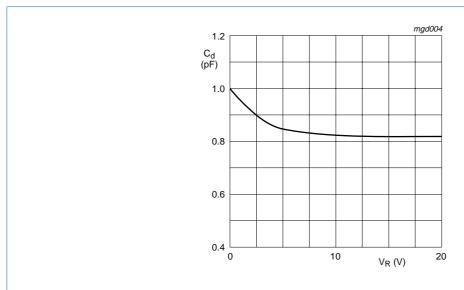
Fig 4. Reverse current as a function of junction temperature

Product data sheet

Philips Semiconductors



High-speed switching diode



 T_j = 25 °C; f = 1 MHz

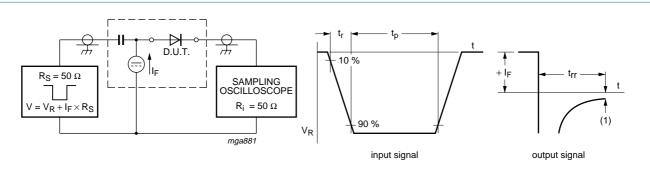
Fig 5. Diode capacitance as a function of reverse voltage; typical values

Philips Semiconductors

BAS32L

High-speed switching diode

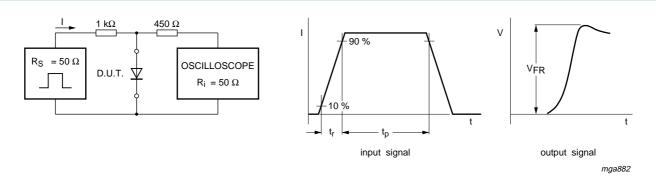
8. Test information



Input signal: Reverse pulse rise time t_r = 0.6 ns; reverse voltage pulse duration t_p = 100 ns; duty factor $\delta \le$ 0.05 Oscilloscope: Rise time t_r = 0.35 ns

(1) $I_R = 1 \text{ mA}$

Fig 6. Reverse recovery time test circuit and waveforms



Input signal: Forward pulse rise time t_r = 20 ns; forward current pulse duration $t_p \ge 100$ ns; duty factor $\delta \le 0.005$

Fig 7. Forward recovery voltage test circuit and waveforms

6 of 11

High-speed switching diode

9. Package outline

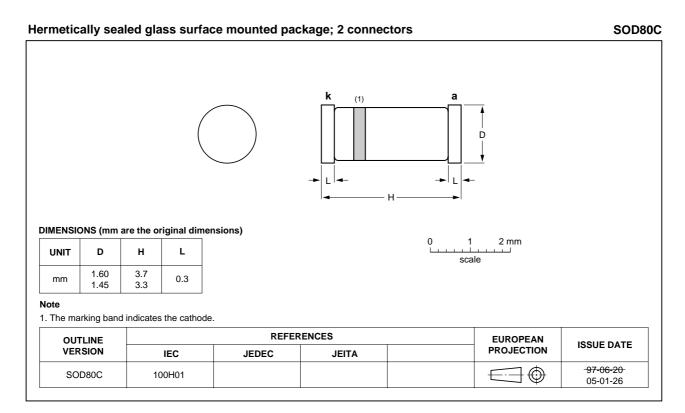


Fig 8. Package outline SOD80C

10. Packing information

Table 8: Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing quantity	
			2500	10000
BAS32L	SOD80C	4 mm pitch, 8 mm tape and reel	-115	-135

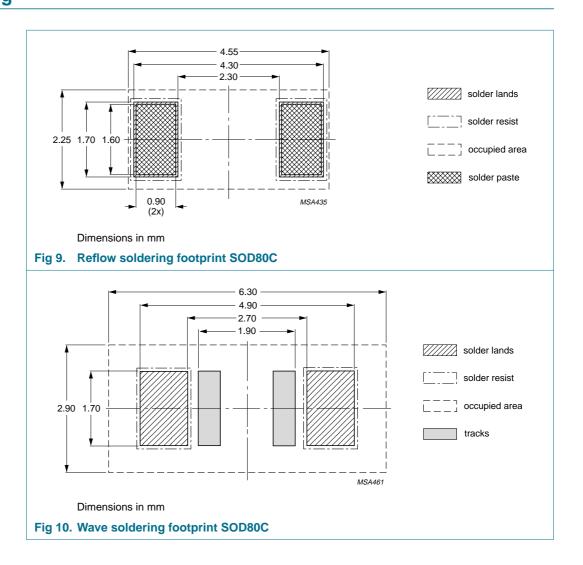
[1] For further information and the availability of packing methods, see $\underline{\text{Section 16}}$.

Philips Semiconductors

BAS32L

High-speed switching diode

11. Soldering



Philips Semiconductors

BAS32L

High-speed switching diode

12. Revision history

Table 9: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
BAS32L_4	20050322	Product data sheet	-	9397 750 14605	BAS32L_3
Modifications:	information	t of this data sheet has be n standard of Philips Ser	•	comply with the nev	v presentation and
	Table 6 "The Rth(j-sp) the	 <u>Section 4 "Marking"</u> added <u>Table 6 "Thermal characteristics"</u> R_{th(j-tp)} thermal resistance from junction to tie-point redefined R_{th(j-sp)} thermal resistance from junction to solder point 			
		"Packing information" a "Soldering" added	auea		
BAS32L_3	20020123	Product specification	-	9397 750 09264	BAS32L_2
BAS32L_2	19960910	Product specification	-	117021	BAS32L_1
BAS32L_1	19960423	Product specification	-	113051	-

Philips Semiconductors

BAS32L

High-speed switching diode

13. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

- [1] Please consult the most recently issued data sheet before initiating or completing a design.
- [2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- [3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

14. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

15. Disclaimers

Life support — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

Right to make changes — Philips Semiconductors reserves the right to make changes in the products - including circuits, standard cells, and/or software - described or contained herein in order to improve design and/or performance. When the product is in full production (status 'Production'), relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no license or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

16. Contact information

For additional information, please visit: http://www.semiconductors.philips.com
For sales office addresses, send an email to: sales.addresses@www.semiconductors.philips.com

10 of 11



High-speed switching diode

17. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications 1
1.4	Quick reference data1
2	Pinning information
3	Ordering information
4	Marking 2
5	Limiting values
6	Thermal characteristics 3
7	Characteristics 3
8	Test information
9	Package outline 7
10	Packing information 7
11	Soldering 8
12	Revision history
13	Data sheet status
14	Definitions
15	Disclaimers
16	Contact information



All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Date of release: 22 March 2005 Document number: 9397 750 14605

